

V_{DSS}	600V
$R_{DS(on)}$ (Max.)	0.196Ω
I_D	20A
P_D	120W

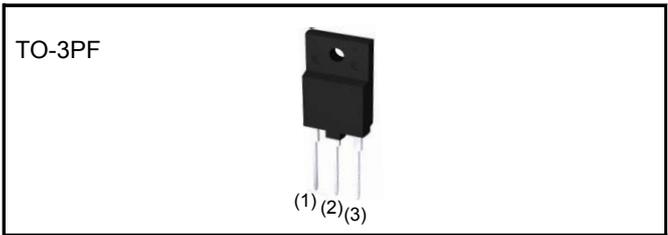
●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be $\pm 20V$.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating ; RoHS compliant

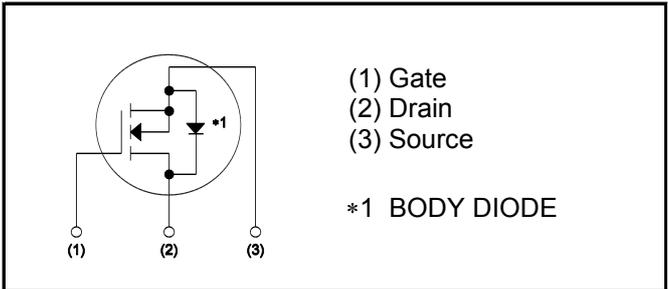
●Application

Switching Power Supply

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Tube
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	360
	Taping code	C8
	Marking	R6020ENZ

●Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Value	Unit	
Drain - Source voltage	V_{DSS}	600	V	
Continuous drain current	$T_c = 25^\circ C$	I_D^{*1}	± 20	A
	$T_c = 100^\circ C$	I_D^{*1}	± 9.4	A
Pulsed drain current	$I_{D,pulse}^{*2}$	± 60	A	
Gate - Source voltage	V_{GSS}	± 20	V	
Avalanche energy, single pulse	E_{AS}^{*3}	418	mJ	
Avalanche energy, repetitive	E_{AR}^{*3}	0.63	mJ	
Avalanche current, repetitive	I_{AR}	3.4	A	
Power dissipation ($T_c = 25^\circ C$)	P_D	120	W	
Junction temperature	T_j	150	$^\circ C$	
Range of storage temperature	T_{stg}	-55 to +150	$^\circ C$	
Reverse diode dv/dt	dv/dt ^{*4}	15	V/ns	

●Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 480V$ $T_j = 25^\circ C$	50	V/ns

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R_{thJC}	-	-	1.04	$^\circ C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	40	$^\circ C/W$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^\circ C$

●Electrical characteristics ($T_a = 25^\circ C$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	600	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$ $T_j = 25^\circ C$	-	0.1	100	μA
		$T_j = 125^\circ C$	-	-	1000	
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	2	-	4	V
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS} = 10V, I_D = 9.5A$ $T_j = 25^\circ C$	-	0.170	0.196	Ω
		$T_j = 125^\circ C$	-	0.360	-	
Gate input resistance	R_G	$f = 1MHz, \text{open drain}$	-	5.8	-	Ω

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Transconductance	g_{fs}^{*5}	$V_{DS} = 10V, I_D = 10A$	5	10	-	S
Input capacitance	C_{iss}	$V_{GS} = 0V$	-	1400	-	pF
Output capacitance	C_{oss}	$V_{DS} = 25V$	-	1200	-	
Reverse transfer capacitance	C_{rss}	$f = 1MHz$	-	130	-	
Effective output capacitance, energy related	$C_{o(er)}$	$V_{GS} = 0V$ $V_{DS} = 0V \text{ to } 480V$	-	56	-	pF
Effective output capacitance, time related	$C_{o(tr)}$		-	266	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx 480V, V_{GS} = 10V$	-	35	-	ns
Rise time	t_r^{*5}	$I_D = 10A$	-	53	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_L = 47.5\Omega$	-	150	-	
Fall time	t_f^{*5}	$R_G = 10\Omega$	-	67	-	

●Gate Charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*5}	$V_{DD} \approx 480V$	-	60	-	nC
Gate - Source charge	Q_{gs}^{*5}	$I_D = 20A$	-	8	-	
Gate - Drain charge	Q_{gd}^{*5}	$V_{GS} = 10V$	-	33	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} \approx 480V, I_D = 20A$	-	6.9	-	V

*1 Limited only by maximum temperature allowed.

*2 $P_W \leq 10\mu s$, Duty cycle $\leq 1\%$

*3 $I_D = 3.4A, V_{DD} = 50V$

*4 Reference measurement circuits Fig.5-1.

*5 Pulsed

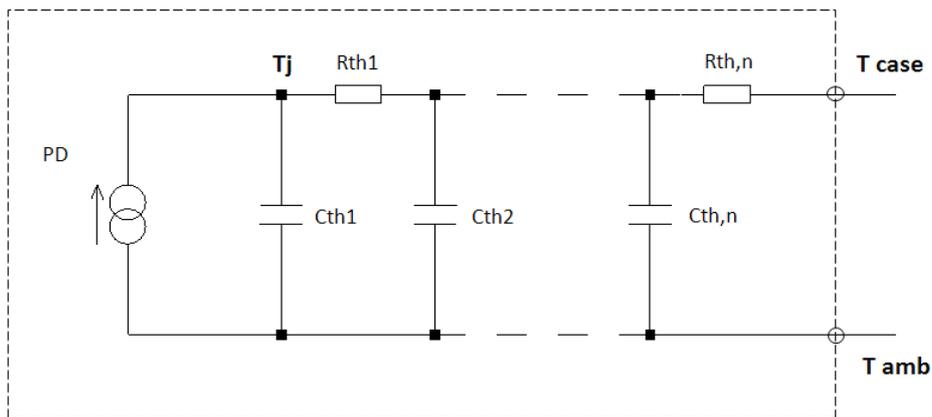
●Body diode electrical characteristics (Source-Drain) ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_S^{*1}	$T_c = 25^\circ\text{C}$	-	-	20	A
Inverse diode direct current, pulsed	I_{SM}^{*2}		-	-	60	A
Forward voltage	V_{SD}^{*5}	$V_{GS} = 0\text{V}, I_S = 10\text{A}$	-	-	1.5	V
Reverse recovery time	t_{rr}^{*5}	$I_S = 20\text{A}$ $di/dt = 100\text{A}/\mu\text{s}$	-	550	-	ns
Reverse recovery charge	Q_{rr}^{*5}		-	10.4	-	μC
Peak reverse recovery current	I_{rrm}^{*5}		-	38	-	A

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R_{th1}	0.129	K/W
R_{th2}	0.627	
R_{th3}	1.22	

Symbol	Value	Unit
C_{th1}	0.00475	Ws/K
C_{th2}	0.0387	
C_{th3}	1.06	



●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

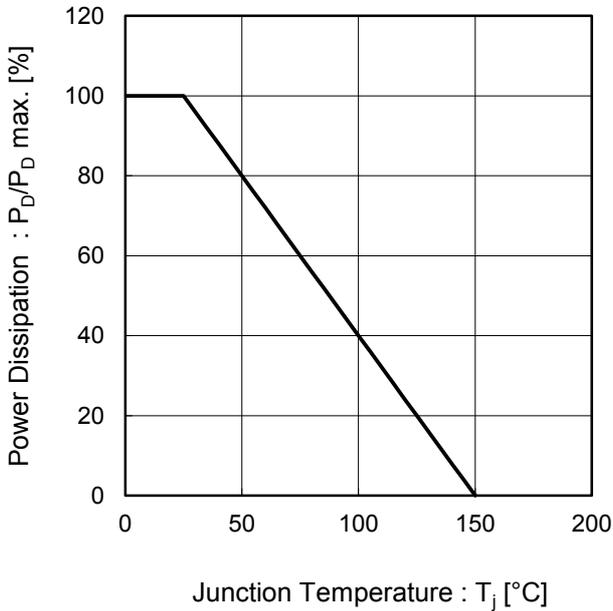


Fig.2 Maximum Safe Operating Area

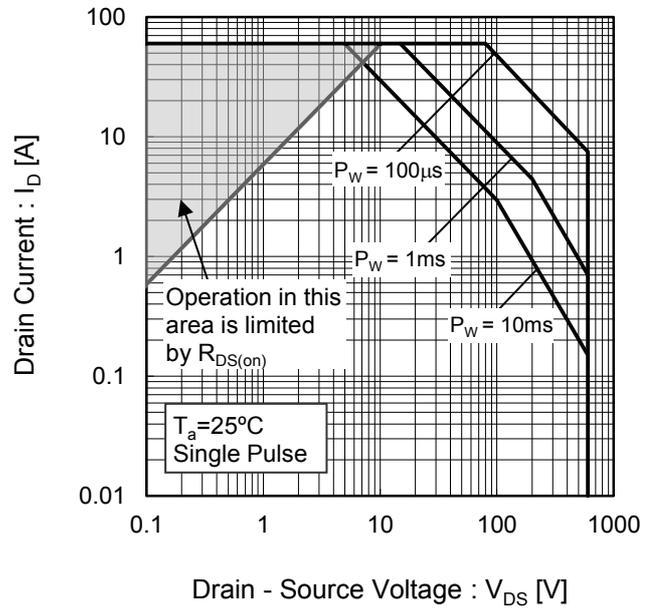


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

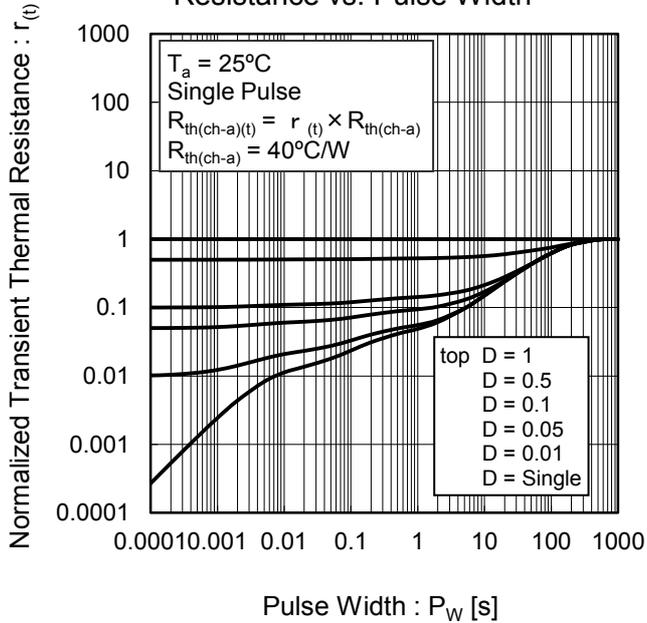
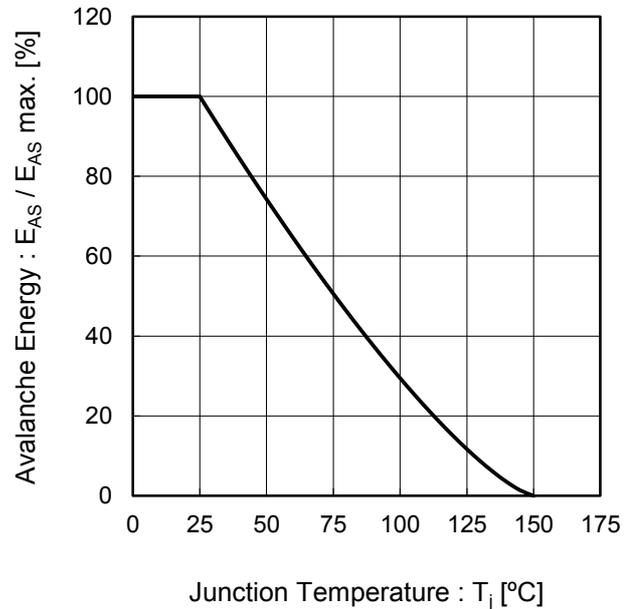


Fig.4 Avalanche Energy Derating Curve vs Junction Temperature



●Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

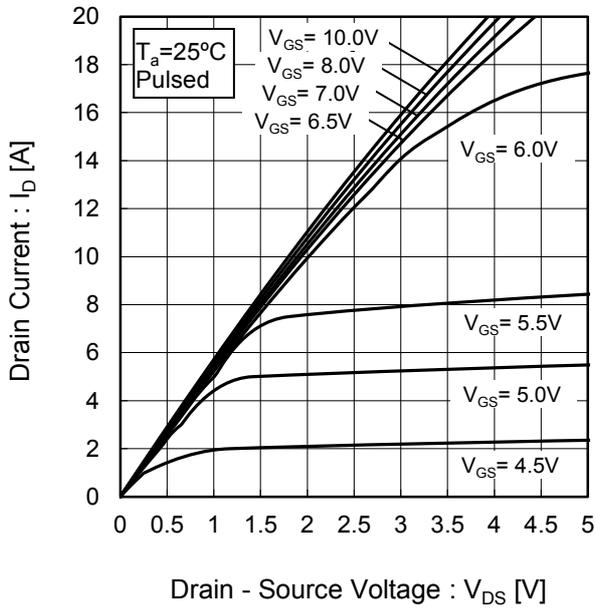


Fig.6 Typical Output Characteristics(II)

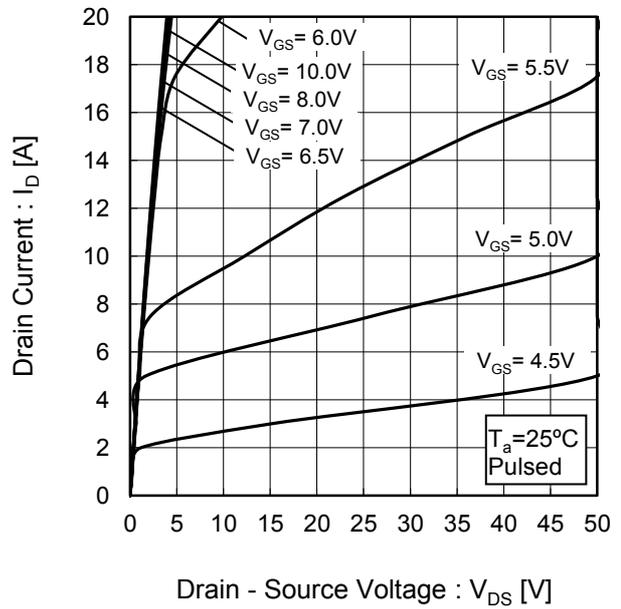


Fig.7 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(I)

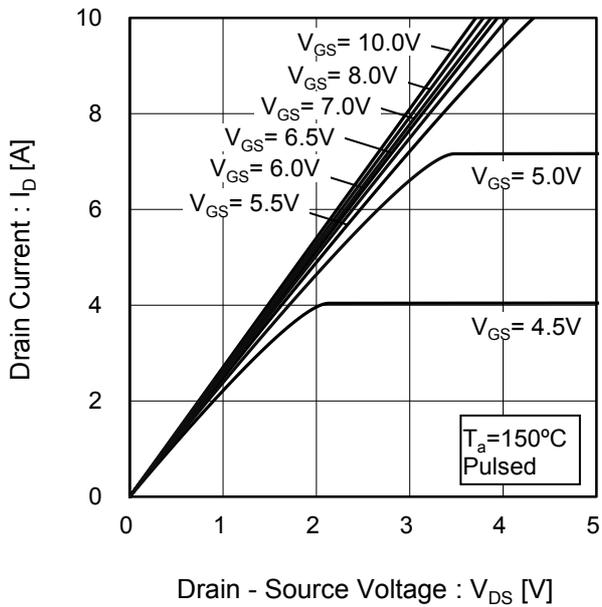
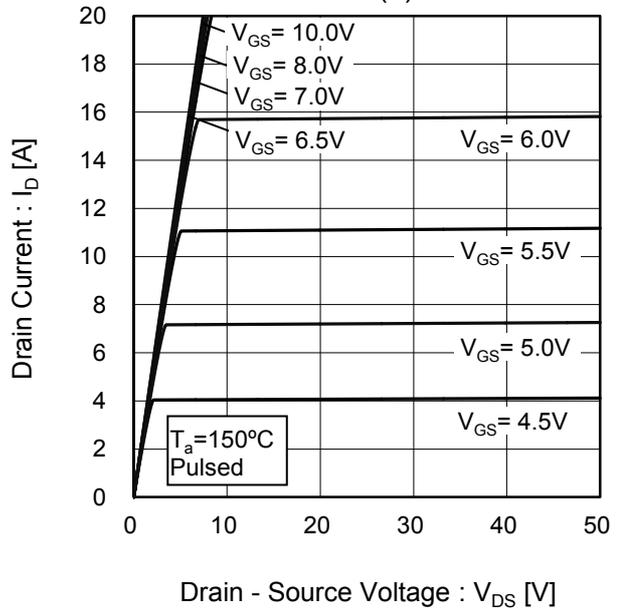


Fig.8 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.9 Breakdown Voltage vs. Junction Temperature

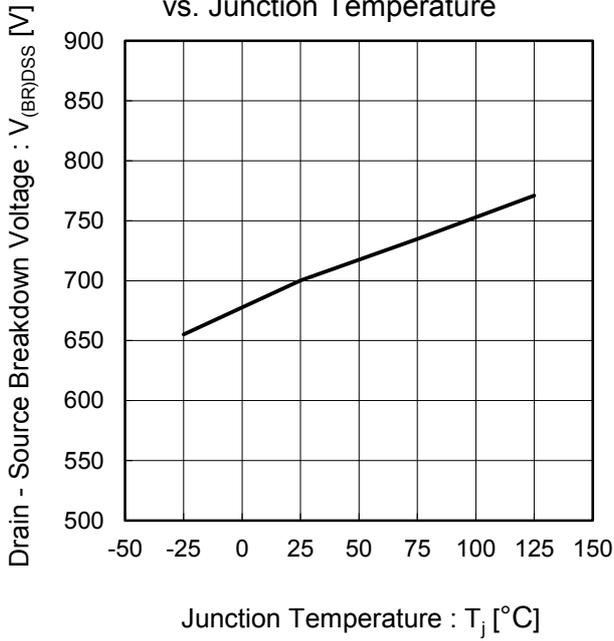


Fig.10 Typical Transfer Characteristics

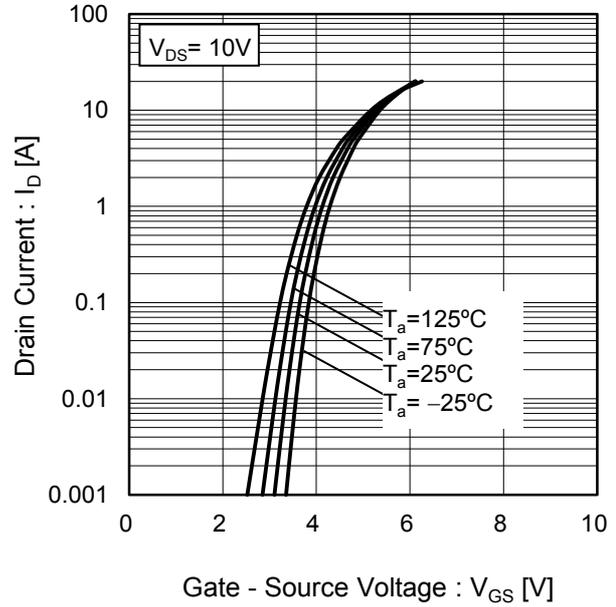


Fig.11 Gate Threshold Voltage vs. Junction Temperature

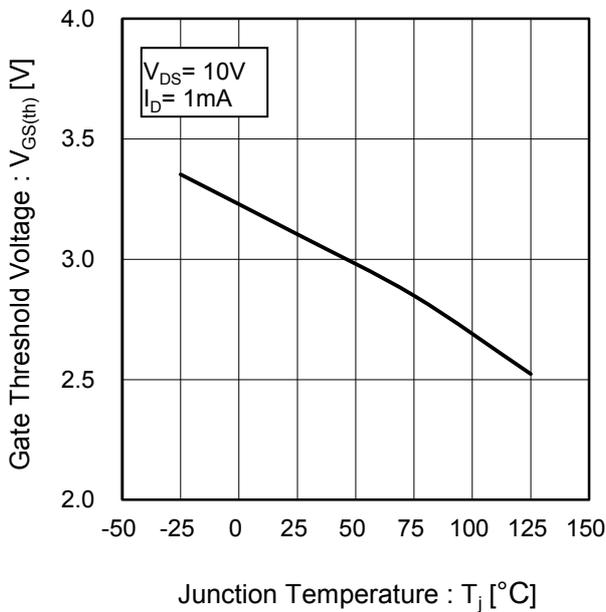
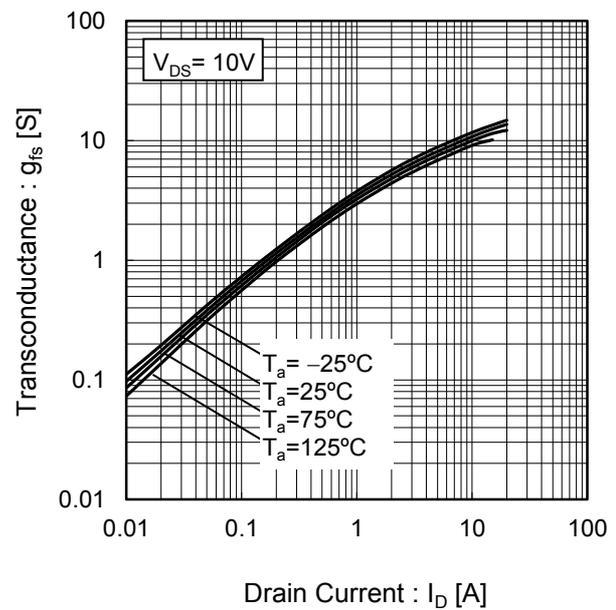


Fig.12 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Gate Source Voltage

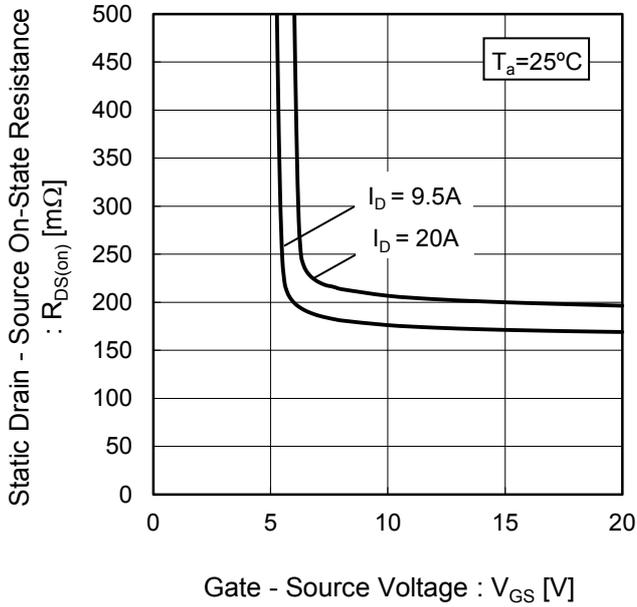


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature

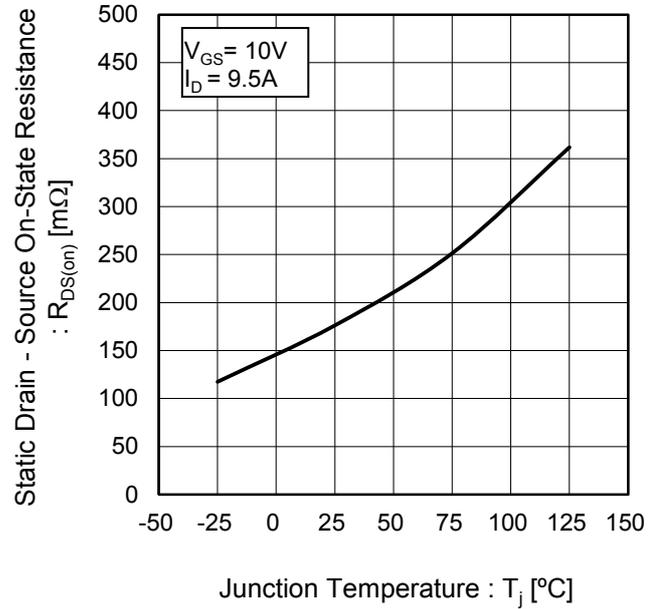


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current

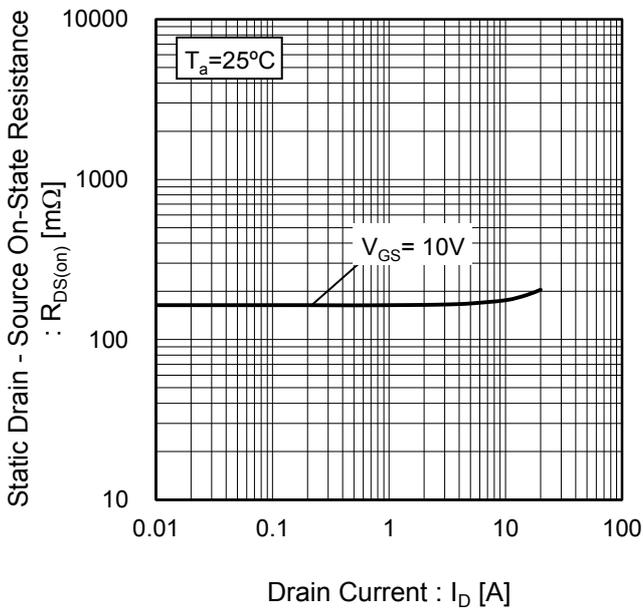
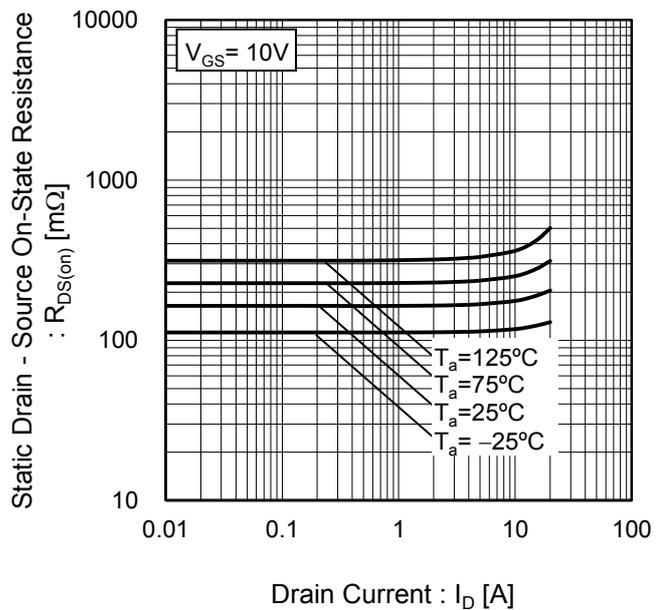


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current



●Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

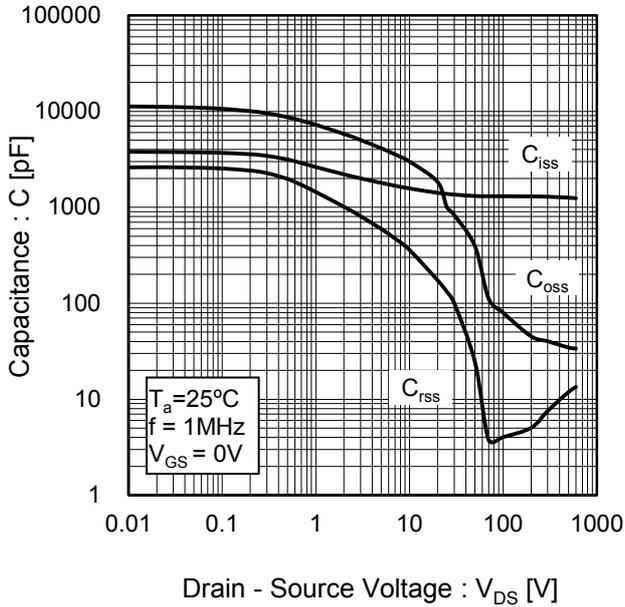


Fig.18 Coss Stored Energy

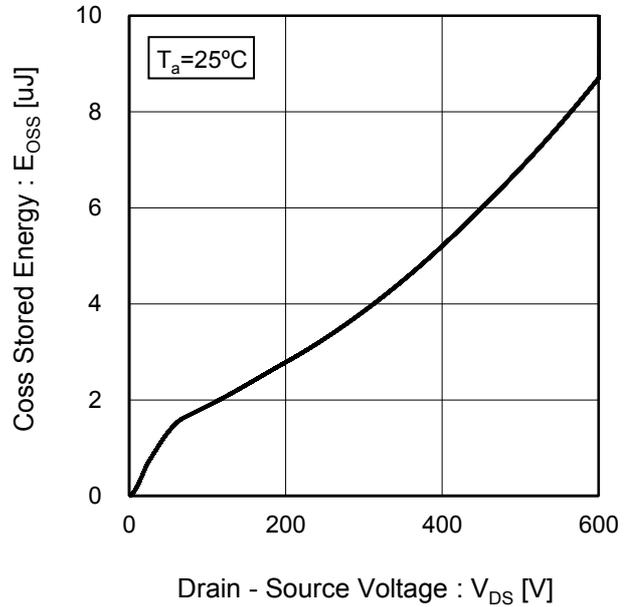


Fig.19 Switching Characteristics

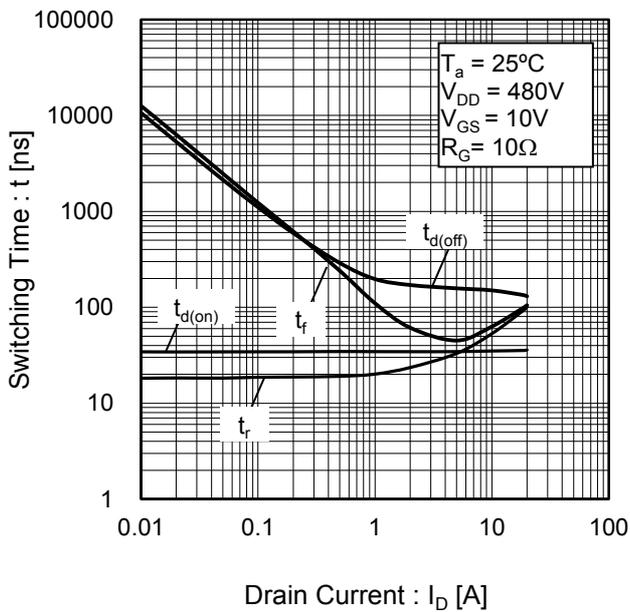
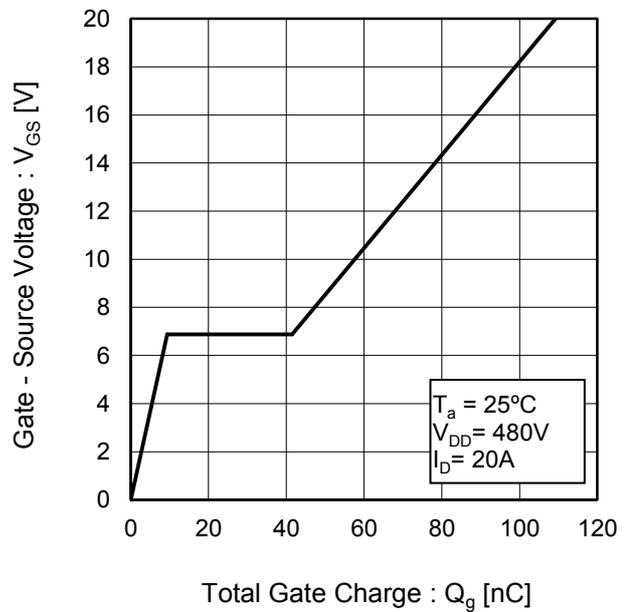


Fig.20 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.21 Inverse Diode Forward Current vs. Source - Drain Voltage

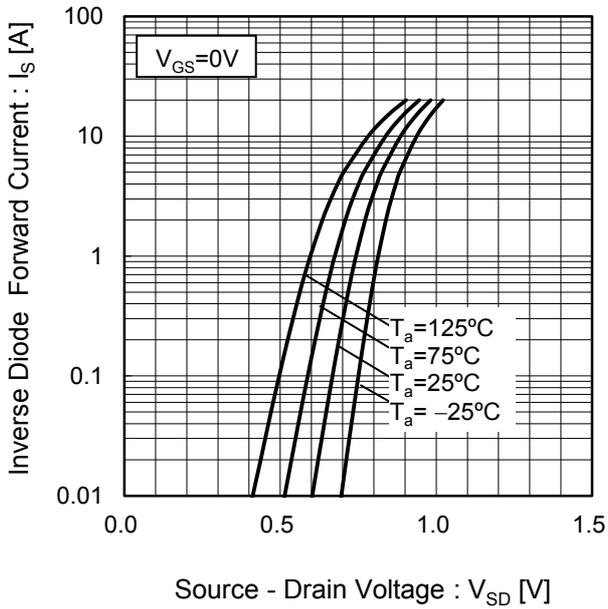
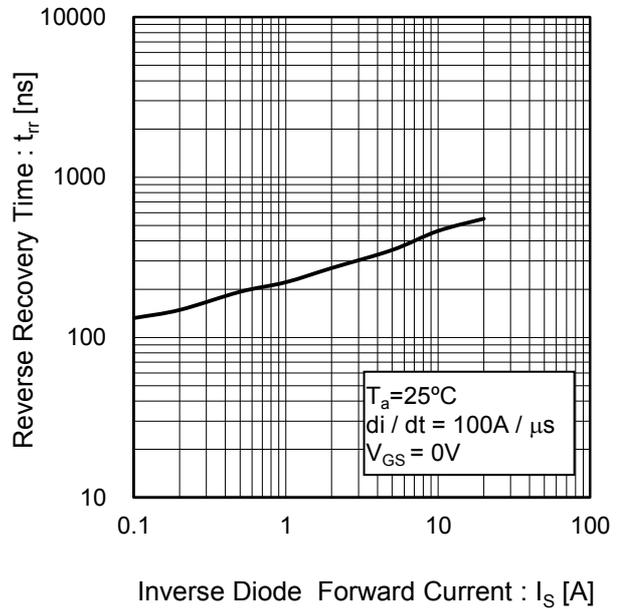


Fig.22 Reverse Recovery Time vs. Inverse Diode Forward Current



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

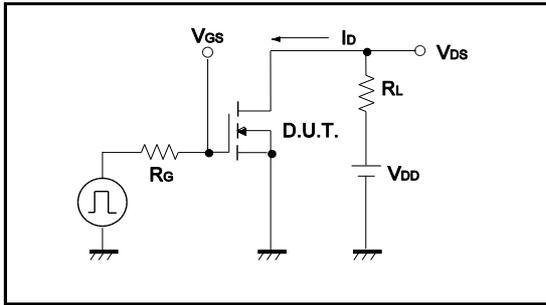


Fig.1-2 Switching Waveforms

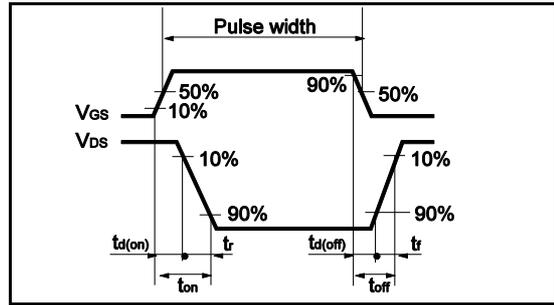


Fig.2-1 Gate Charge Measurement Circuit

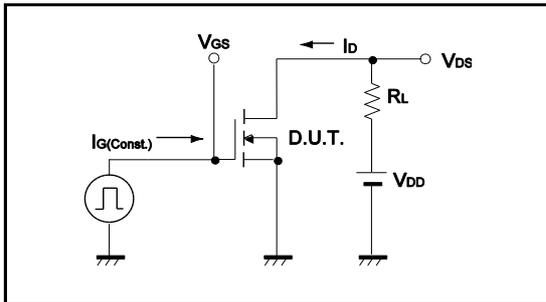


Fig.2-2 Gate Charge Waveform

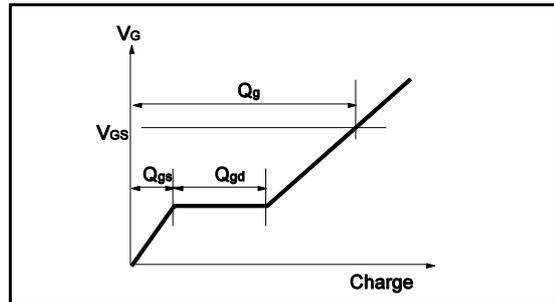


Fig.3-1 Avalanche Measurement Circuit

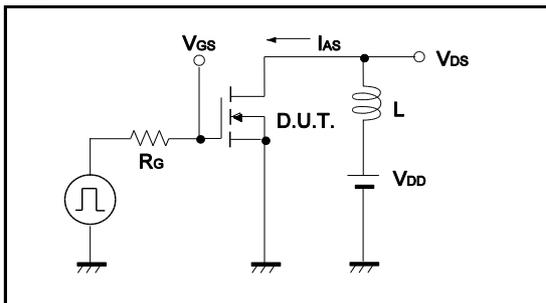


Fig.3-2 Avalanche Waveform

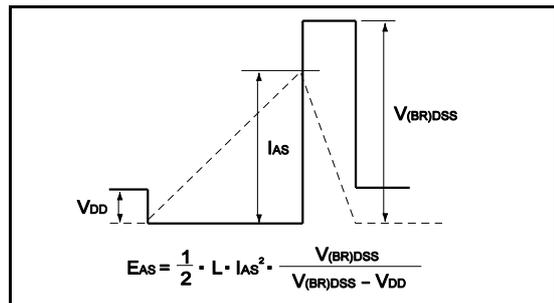


Fig.4-1 dv/dt Measurement Circuit

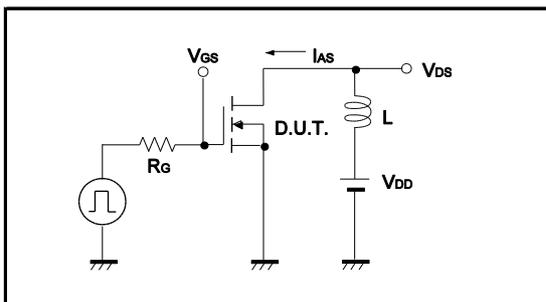


Fig.4-2 dv/dt Waveform

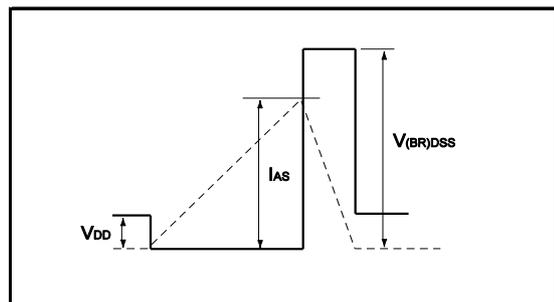


Fig.5-1 di/dt Measurement Circuit

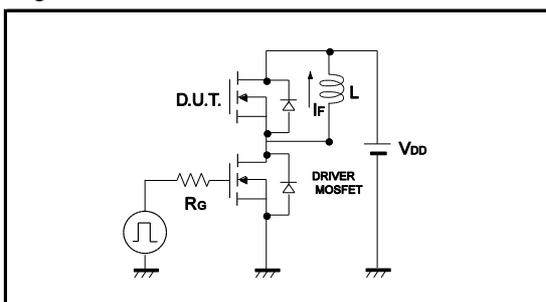
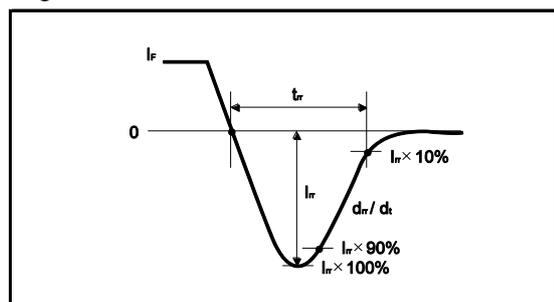
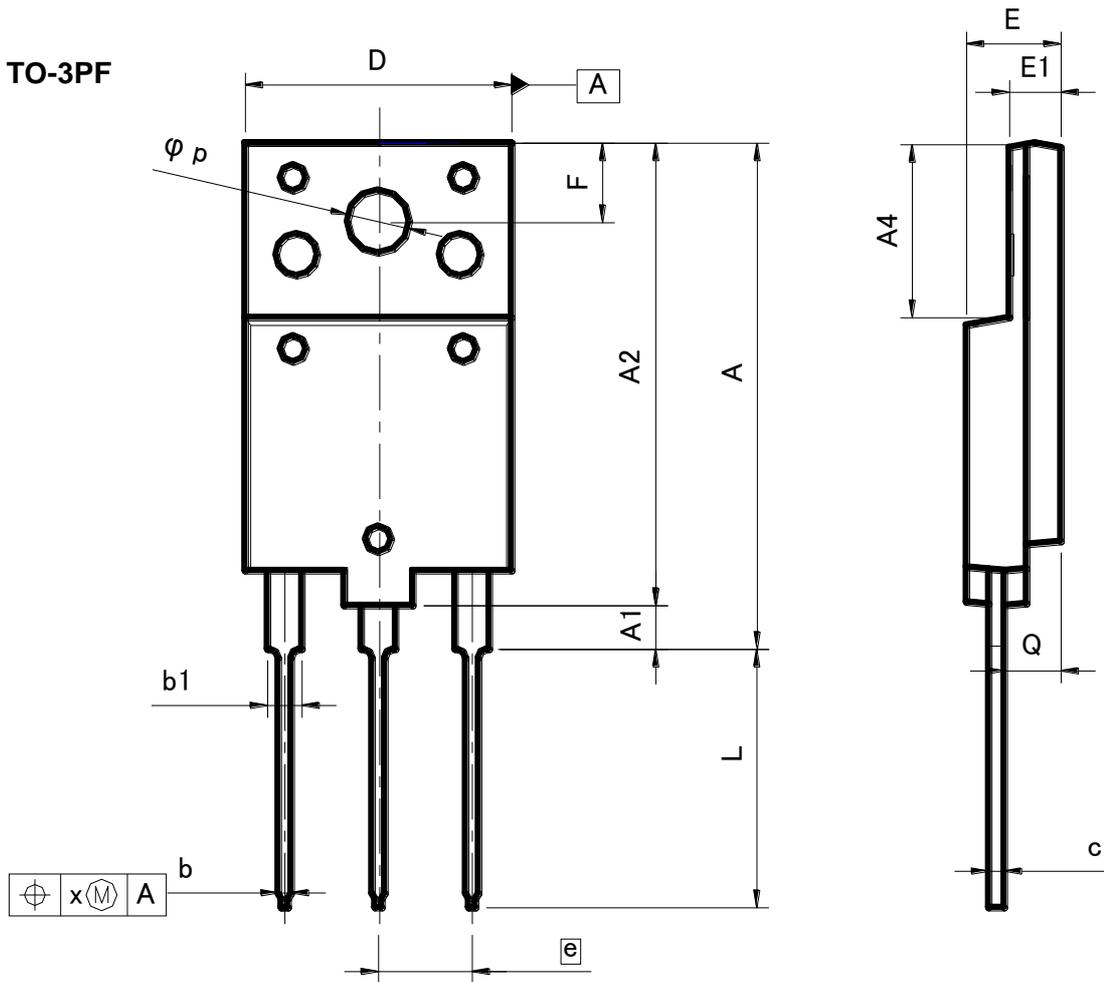


Fig.5-2 di/dt Waveform



●Dimensions (Unit : mm)



Dimension in mm / inches

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- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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